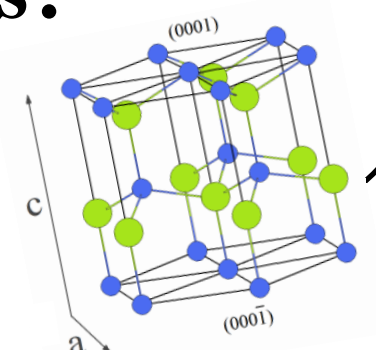


Why ZnO/ZnMgO structures?

- Wide direct band gap 3.37eV to 4.0eV (at 300K)
- Large 60 meV exciton binding energy (ZnO)
- Stable excitonic emission at room temperature
- Cheaper alternative to GaN
- Compatible with GaN due to its crystal symmetry, large exciton binding energy and large band gap comparable
- Excellent candidate for use in visible and ultraviolet light emitters and detectors.



What do we want to show?

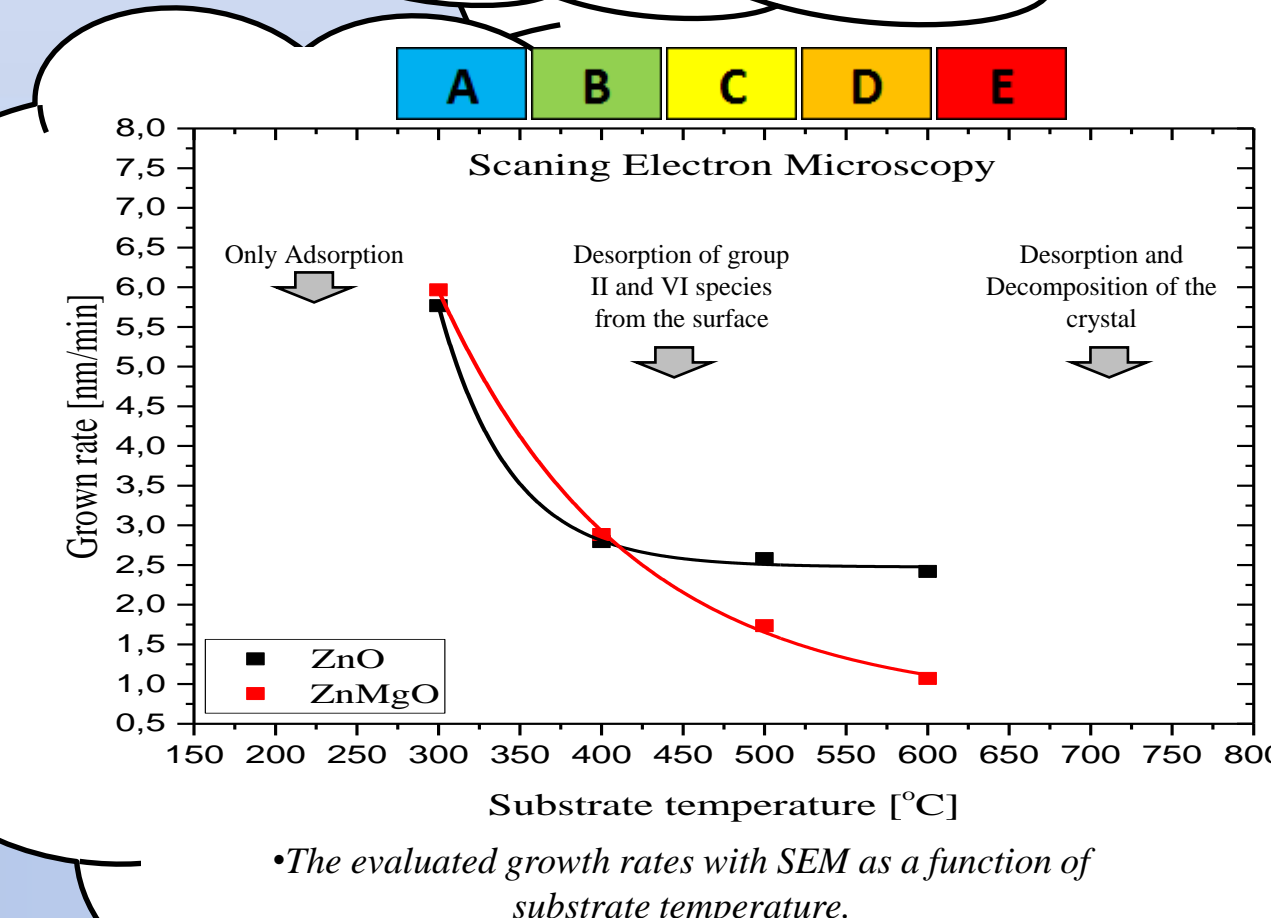
- The aim of our work is to investigate influence of substrate temperature on incorporation of magnesium into ZnMgO layers grown by PA-MBE.

How to show it?

- Make a set of ZnO/ZnMgO layers by MBE at the same growth conditions but at different substrate temperature.
- Estimate Mg content in ZnMgO layers by Photoluminescence and X-Ray Diffraction.

What structures were made?

What about growth rate?

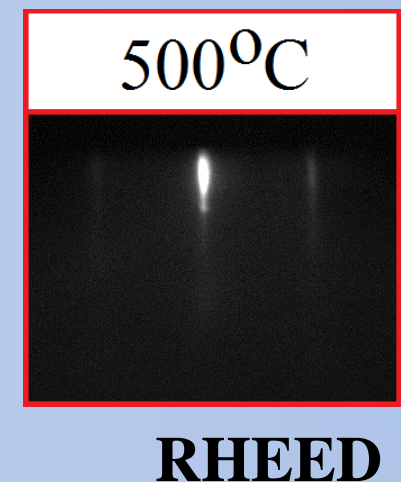


Sample	Temperature (°C)
A	300
B	400
C	450
D	500
E	600

Why concentration of Mg in ZnMgO layers rise with substrate temperature?



Substrate Temperature Changed in range: 300°C-600°C



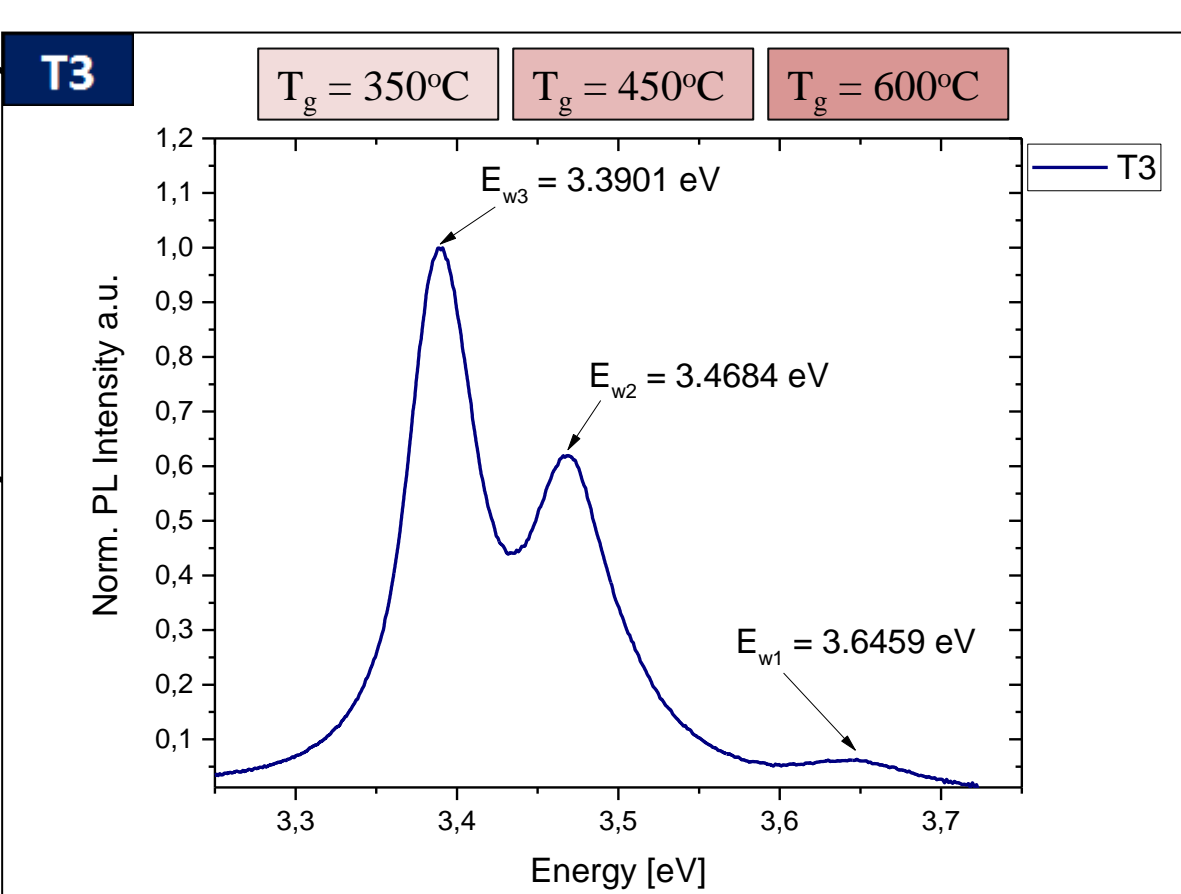
Magnesium Flux Constant

Zinc Flux Constant

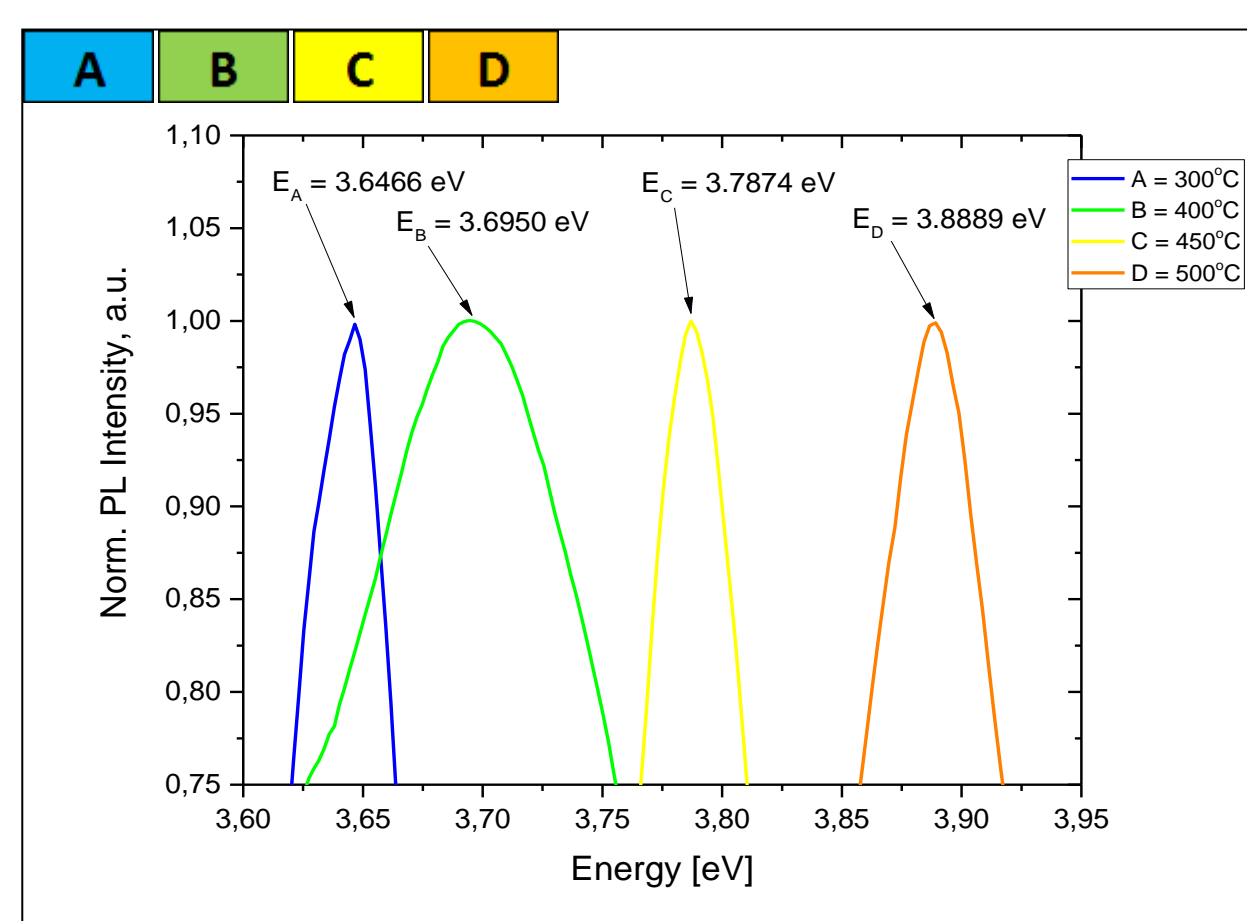
Oxygen Flux Constant

What are the evidence for the influence of substrate temperature on Mg concentration in ZnMgO layers?

Photoluminescence



* Photoluminescence spectra for ZnMgO thin films at 10 K.



* Photoluminescence spectra for ZnMgO thin films at 10 K.

We used the following equation to estimate the composition of Mg in Zn_{1-x}Mg_xO layers:

$$E_{PL} = 1,51x + 3,36\text{eV}$$

The above equation is a fit to the results of PL, where precise determination of the Mg concentration x was performed by elastic recoil detection analysis ERD:

B. Laumer, et. al., J. Appl. Phys. 133, 233512(2013)

	Temp. [°C]	Energy [eV]	Composition of Mg [%]
T3	350	3.3901	1,99
w1	600	3.6459	18,93
w2	450	3.4684	7,18
w3	350	3.3901	1,99
A	300	3.6466	18,98
B	400	3,695	22,19
C	450	3,7874	28,30
D	500	3,8889	35,03
E	600	?	?

How to explain evolution of growth rates as a function of substrate temperature?

- Perhaps by Sticking Coefficient.

$$Sc = \frac{N_{ads}}{N_{tot}}$$

A Sc for Oxygen is independent of substrate temperature but a Sc for metal elements is inversely proportional to the exponential of the temperature and also inversely proportional to the square of the distance between atomic steps on the surface of a crystalline material.

How to check whether ZnO decomposition takes place?

The decomposition rate of ZnO in vacuum can be measured in the same way as in work: N. Grandjean, Appl. Phys. Lett. 74, 1854. To estimate the decomposition rate below equation was used:

$$V_d = \frac{\beta}{\alpha} V_g$$

N. Grandjean, Appl. Phys. Lett. 74, 1854

In the range of temperatures used in our case, the decomposition rate is negligible ~0.05 nm/min.

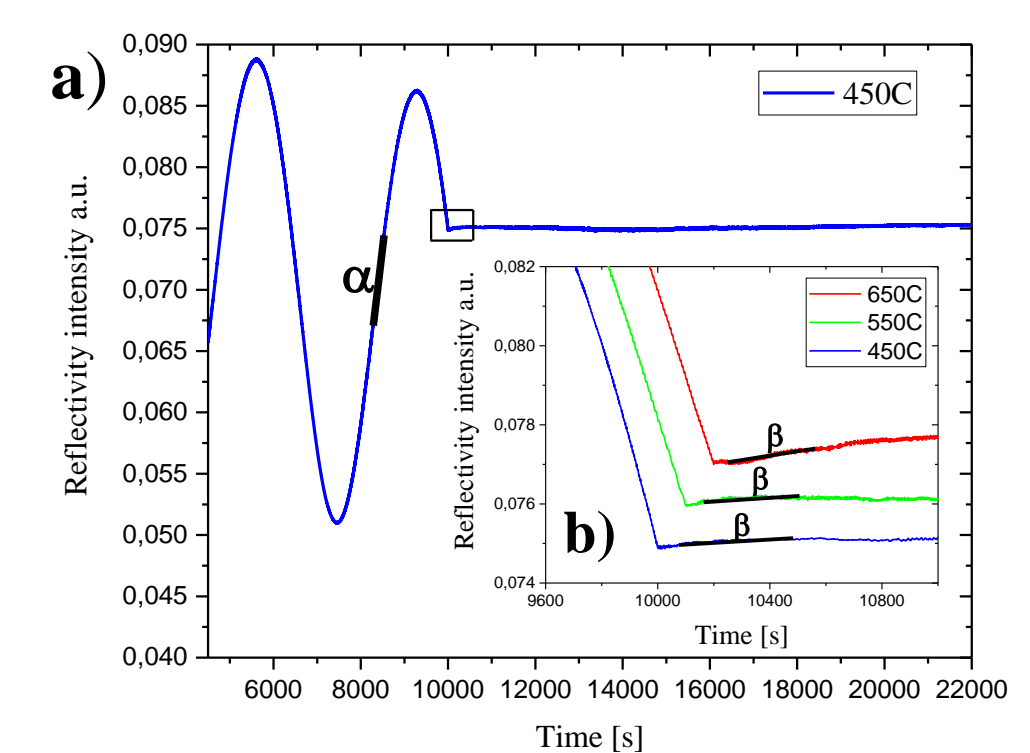


Fig. a) Reflectivity intensity oscillations recorded during growth of ZnO at 450°C. b) Reflectivity intensity variation during evaporation of ZnO in vacuum as a function substrate temperature. The slopes α and β are proportional to the growth rate and to the evaporation rate, respectively.

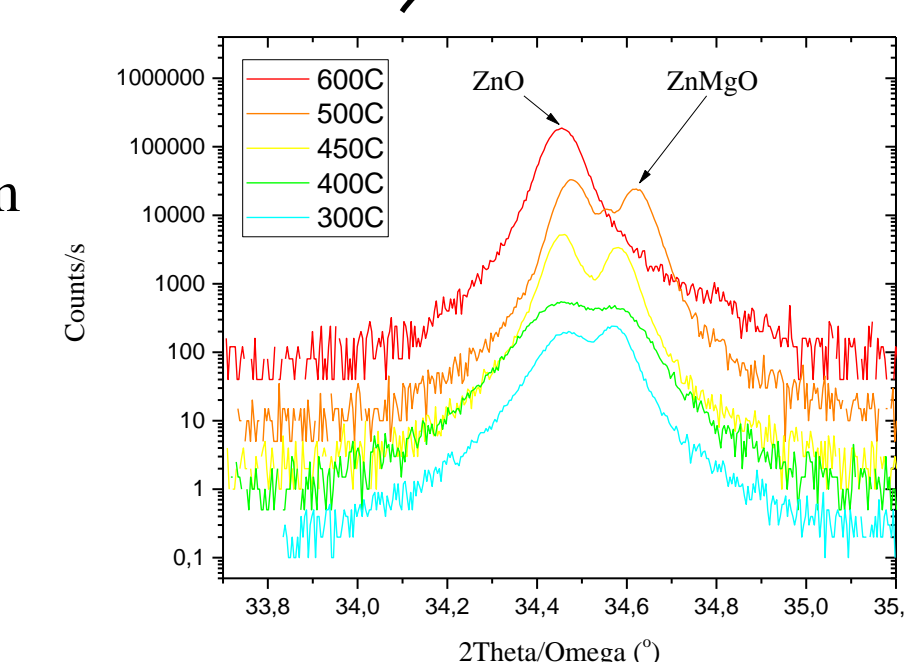
X-Ray Diffraction

The composition of magnesium calculated from the Vegard's law:

$$x_c = \frac{c(x_c)_{ZnMgO} - c_{ZnO}}{c_{MgO} - c_{ZnO}} * 100\%$$

Ref. Schleife A. Fuchs F. Furthmüller J. Bechstedt F 2006 Phys. Rev. B 73 245212

$$c_{MgO} = 5.136A$$



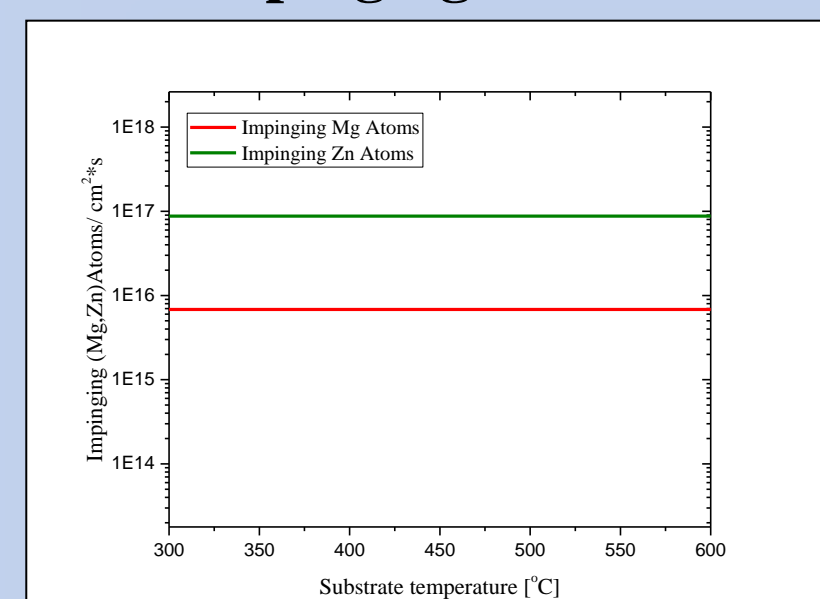
* X-ray diffraction 2θ/ω scans of 00.2 ZnO/ZnMgO symmetrical reflection of ZnO/ZnMgO epitaxial layers on a-plane sapphire.

	Temp. [°C]	C [A]	Composition of Mg [%]
A	300	5,1857	20,35
B	400	5,1847	21,96
C	450	5,1831	25,12
D	500	5,1779	33,39
E	600	?	?

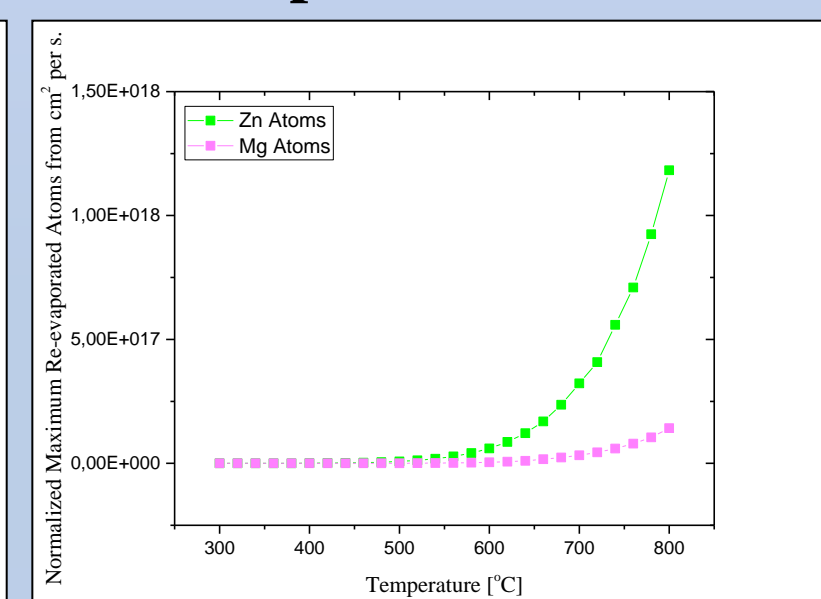
Discussion

The composition variation in the alloys as a function of the growth temperature can be explained by the difference of vapor pressure between Mg and Zn elements at high growth temperatures. Due to the higher saturation pressure of Zn vapor, Zn atoms can be easily re-evaporated at higher growth temperature yielding Mg enriched films. Effectively, higher Mg concentration in the alloy films are obtained when grown at higher temperatures.

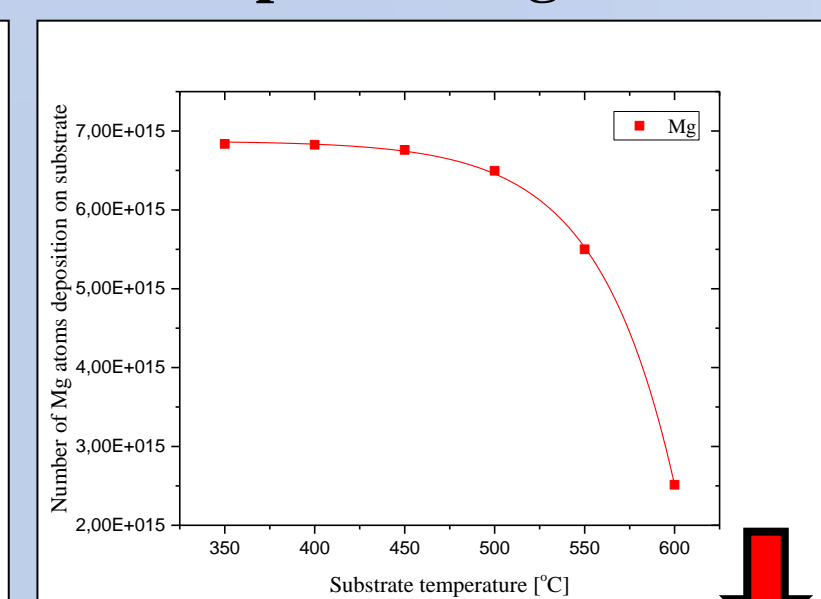
What about Impinging Atoms?



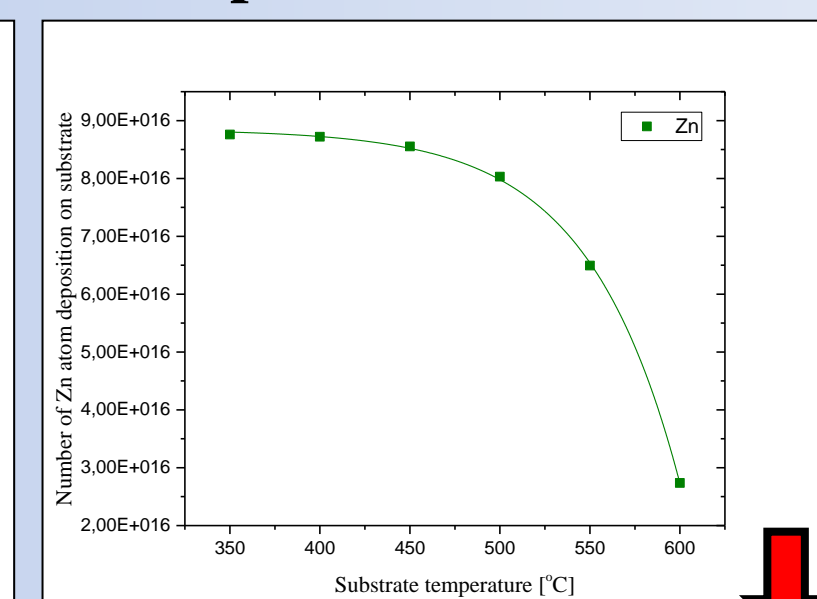
What about Re-evaporation Atoms?



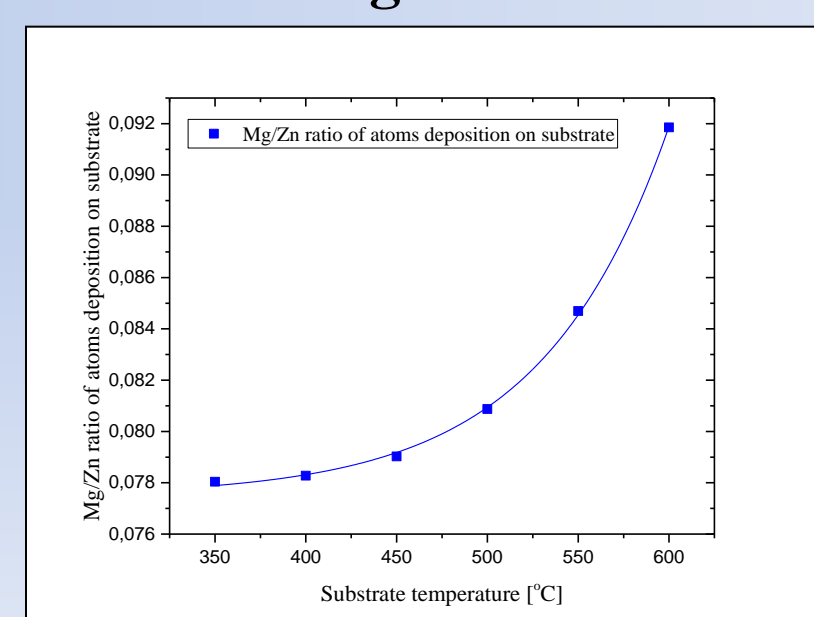
What about Deposited Mg Atoms?



What about Deposited Zn Atoms?



What about Mg/Zn Atom Ratio?



Where:
Flux Zn [Pa/s]
Flux Mg [Pa/s]
 M_{AZn} Zn atomic Mass [kg].
 M_{AMg} Mg atomic Mass [kg].
 $M(i)$ and $p(i)$ are gram-molecular weight and equilibrium partial pressure of vapor species i, and R and T are the molar gas constant and absolute temperature. N_A is the Avogadro constant.
 W_n - normalization factor.

$$\text{Impinging Atoms } Mg = \frac{\text{FluxMg}}{M_{AMg}} * 10000\text{cm}^2$$

$$\text{Impinging Atoms } Zn = \frac{\text{FluxZn}}{M_{AZn}} * 10000\text{cm}^2$$

$$\text{Re-evaporated Atoms} = W_n * \frac{p(i)}{[2\pi M(i)RT]^{1/2}} * N_A$$

$$(Mg, Zn) \text{ Deposition Atoms} = \text{Impinging Atoms } (Mg, Zn) - \text{Re-evaporated Atoms } (Mg, Zn)$$

Summary:

• The MBE Zn_{1-x}Mg_xO and ZnO layers were characterised with various techniques (RHEED, Laser Reflection Interferometry, PL, XRD, SEM) to estimate their optical and structural properties.

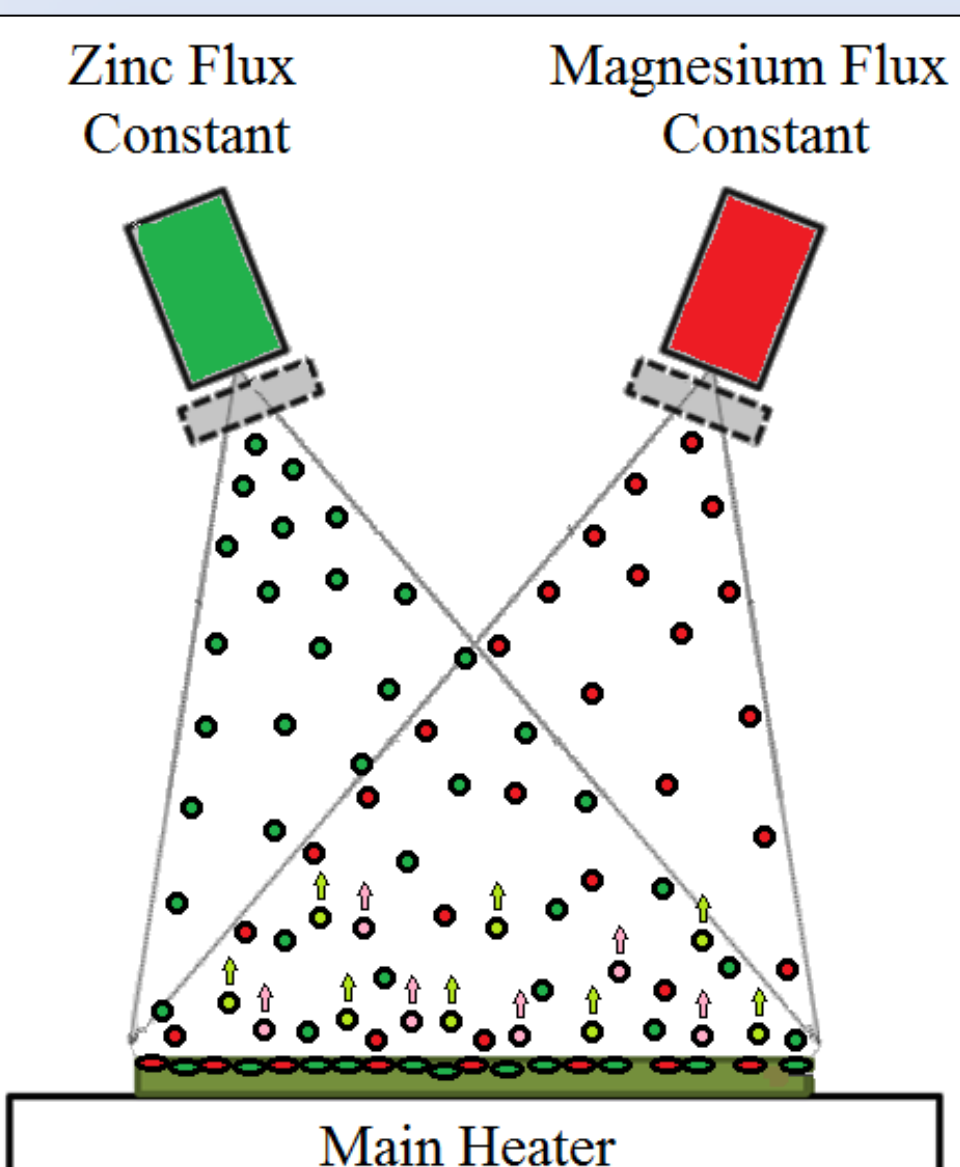
• XRD and PL measurements allowed to calculate the Mg content in the ZnMgO layers. The results obtained with different techniques are consistent.

• The influence of the substrate temperature on the Mg concentration is evident and well documented.

• The increased concentration of Mg at higher substrate temperatures is caused by different (higher) desorption coefficient of Zn to Mg.

Acknowledgement :

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Substrate Temperature Changed in range: 300°C-600°C

- Impinging Mg Atoms.
- Impinging Zn Atoms.
- Re-evaporated Mg Atoms.
- Re-evaporated Zn Atoms.
- Mg Atoms Deposition.
- Zn Atoms Deposition.